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AND A SUBSTRATE WAFER FOR BUILDING GROUP III-V DEVICES THEREON

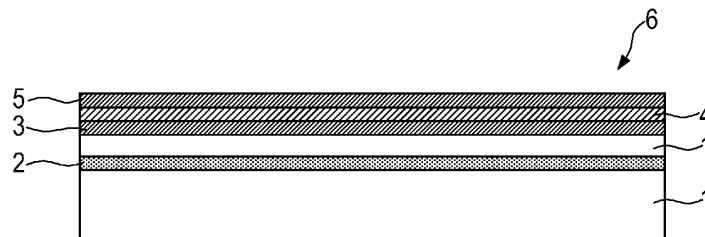


Fig. 1

(57) Abstract: A method for manufacturing a substrate wafer for building group III-V devices thereon, comprising providing a silicon single crystal wafer; forming a gettering region below a top surface of the silicon single crystal wafer; forming a nitrogen enriched passivation layer representing a top portion of the substrate wafer.

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